

# Switching diode

## DAN217U / BAV99U \*1 / DAN217

\*1 BAV99U is only sold in countries other than Japan.

### ●Application

Ultra high speed switching

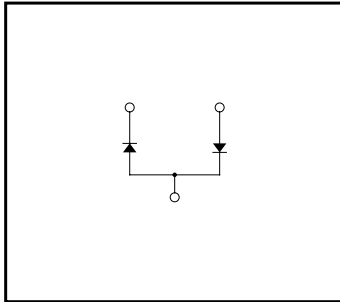
### ●Features

- 1) Small surface mounting type. (UMD3,SMD3)
- 2) Two diode elements are connected in series  
( $V_F \times 2$ ) per circuit.

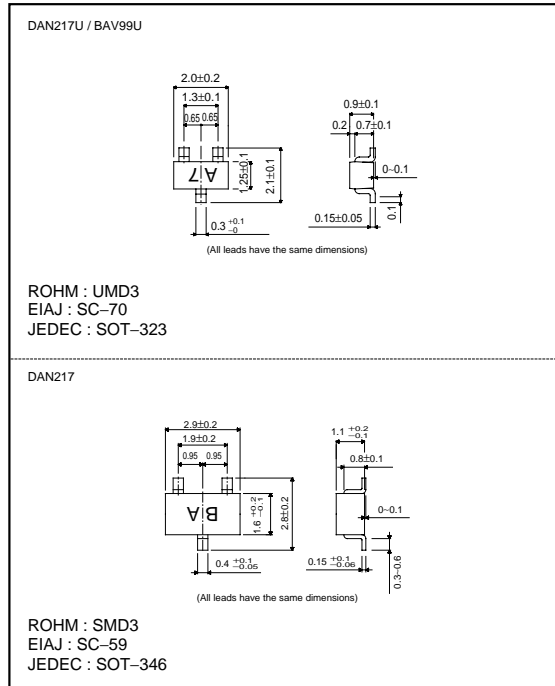
### ●Construction

Silicon epitaxial planar

### ●Circuit



### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Type	Peak reverse voltage $V_{RM}(V)$	DC reverse voltage $V_R(V)$	Peak forward current $I_{FM}(mA)$	Mean rectifying current $I_o(mA)$	Surge current (1 $\mu$ s) $I_{surge}(mA)$	Power dissipation (TOTAL) $P_d(mW)$	Junction temperature $T_j(^{\circ}C)$	Storage temperature $T_{stg}(^{\circ}C)$
DAN217U	80	80	300	100	4000	200	150	-55 ~ +150
BAV99U	80	80	300	100	4000	200	150	-55 ~ +150
DAN217	80	80	300	100	4000	200	150	-55 ~ +150

Diodes

●Electrical characteristics (Ta=25°C)

Type	Forward voltage		Reverse current		Fig
	V <sub>F</sub> (V) Max.	Cond. I <sub>F</sub> (mA)	I <sub>R</sub> (μA) Max.	Cond. V <sub>R</sub> (V)	
DAN217U	1.2	100	0.2	70	1 ~ 3
BAV99U	1.2	100	0.2	70	1 ~ 3
DAN217	1.2	100	0.1	70	4 ~ 6

●Electrical characteristic curves (Ta=25°C)

(DAN217U,BAV99U)---Fig.1~3

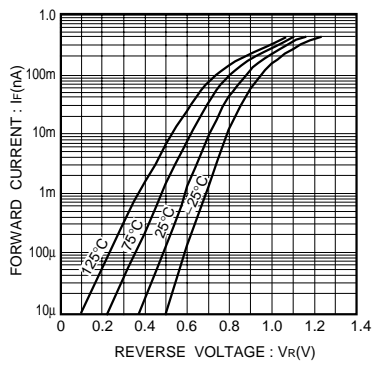


Fig.1 Forward characteristics

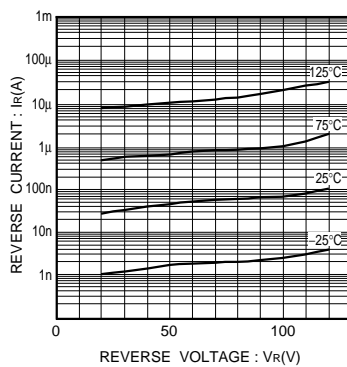


Fig.2 Reverse characteristics

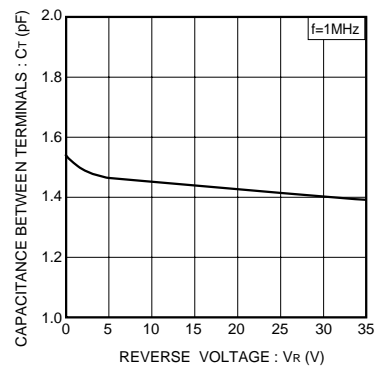


Fig.3 Capacitance between terminals characteristics

(DAN217) ---Fig.4-6

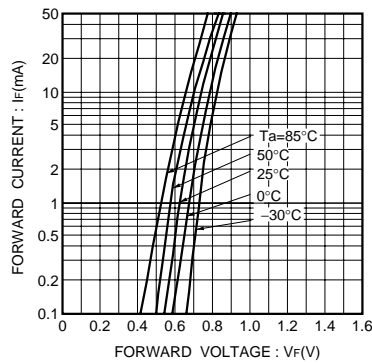


Fig.4 Forward characteristics

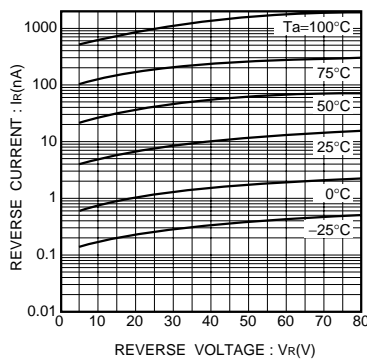


Fig.5 Reverse characteristics

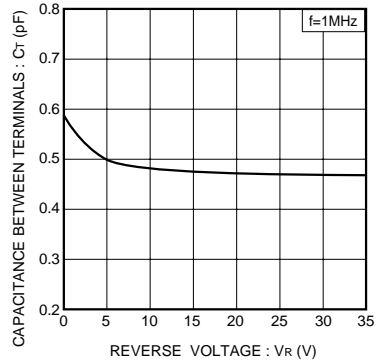


Fig.6 Capacitance between terminals characteristics

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.